

Electronic Supplementary Information

A Simple Approach to the Fabrication of Fluorine-Doped Zinc Oxide Thin Films by Atomic Layer Deposition at Low Temperatures and an Investigation into the Growth Mode

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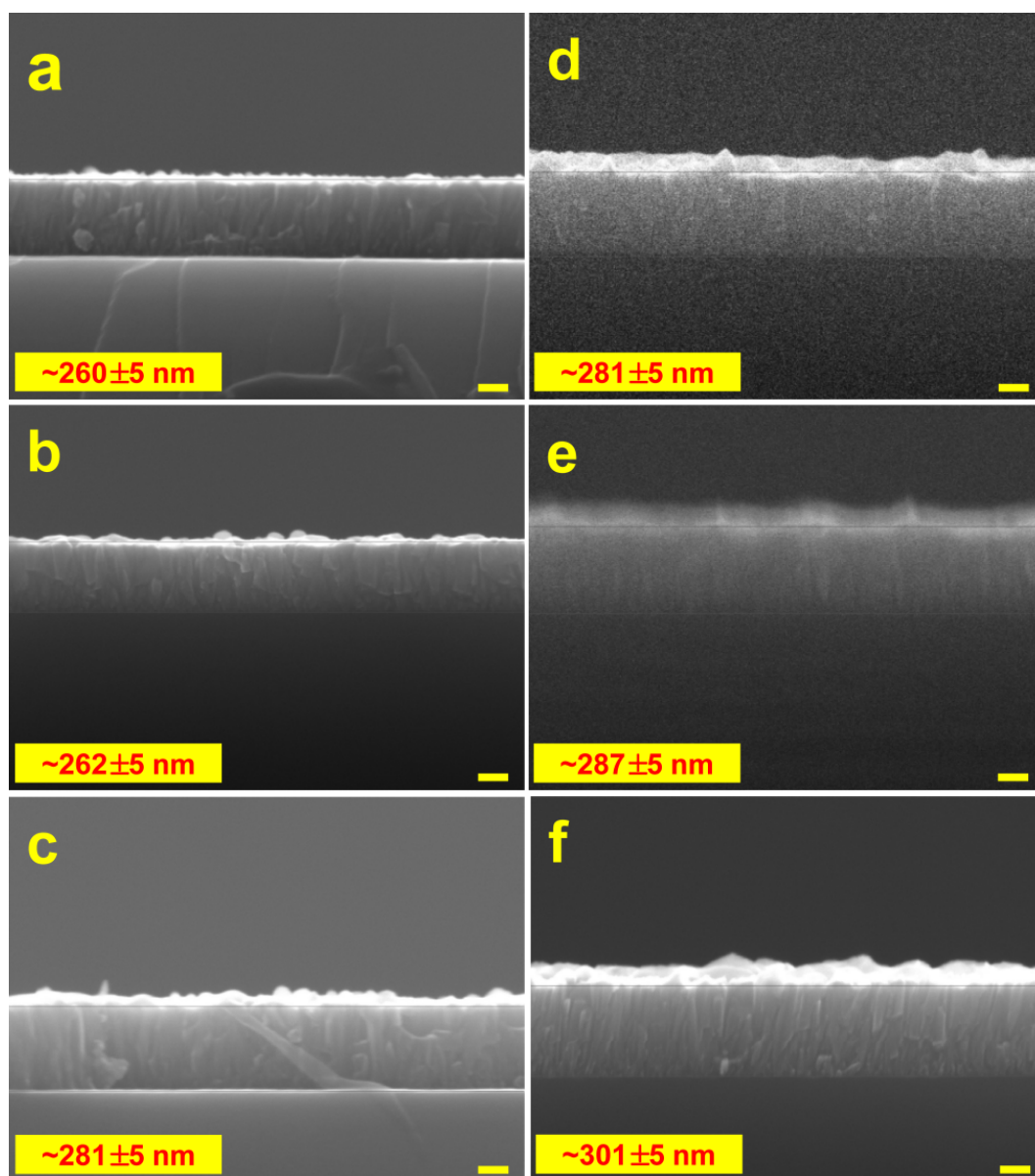


Figure S1. Cross-sectional field emission scanning electron microscopy (FE-SEM) images of (a) undoped ZnO, (b) ZnO:F{0.2}, (c) ZnO:F(0.5), (d) ZnO:F(0.7), (e) ZnO:F(1.0), and (f) ZnO:F(1.2) films grown at 140°C on Si substrates (All scale bars represent 100 nm).

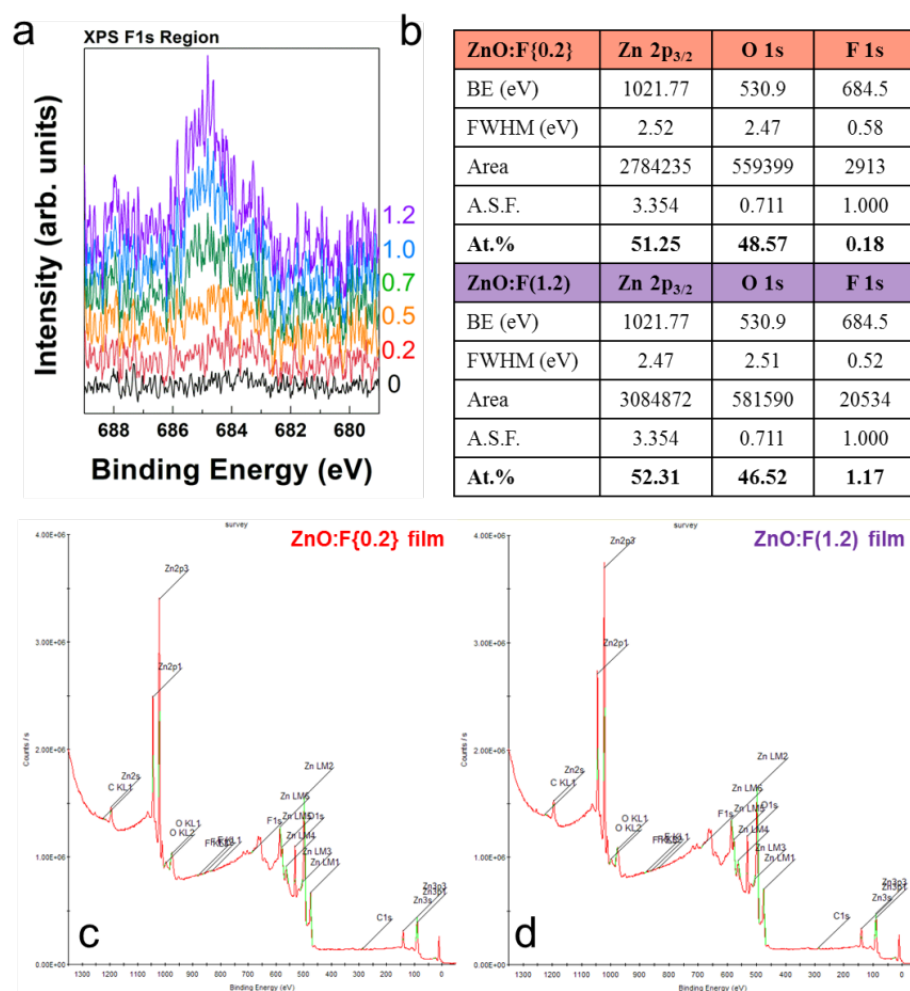


Figure S2. (a) The overlay of XPS spectra for undoped ZnO and various contents of ZnO:F films in F 1s region and (b) the peak-fit results (FWHM; full-width at half-maximum and A.S.F.; atomic sensitivity factor for X-ray sources at 90°) of Zn 2p_{3/2}, O1s, and F1s peaks for ZnO:F{0.2} and ZnO:F(1.2) samples. The XPS spectra of wide scan for (c) ZnO:F{0.2} and (d) ZnO:F(1.2) films are used for the elemental analysis by using the peak fitting program (Thermo Advantage v3.25).

Table S1. Average crystallite sizes of the samples calculated by using the full-width at half-maximum of (100) and (002) peaks, Hall effect measurement parameters (carrier concentration (*n*), mobility (*μ*), resistivity (*ρ*), and conductivity (*σ*)).

Sample I.D.	(100) Crystallite Size (nm)	(002) Crystallite Size (nm)	<i>n</i> (cm ⁻³)	<i>μ</i> (cm ² /Vs)	<i>ρ</i> at RT (Ωcm)	<i>σ</i> at RT (Ωcm) ⁻¹
ZnO	20.77	21.79	1.713×10 ¹⁹	17.73	2.055×10 ⁻²	48.66
ZnO:F{0.2}	19.32	22.32	3.589×10 ¹⁹	43.66	3.983×10 ⁻³	251.1
ZnO:F(0.5)	22.90	23.99	5.467×10 ¹⁹	32.49	3.514×10 ⁻³	284.6
ZnO:F(0.7)	21.93	22.14	1.243×10 ²⁰	25.04	2.181×10 ⁻³	458.6
ZnO:F(1.0)	22.84	23.71	1.375×10 ²⁰	24.20	1.876×10 ⁻³	533.1
ZnO:F(1.2)	21.81	23.51	1.462×10 ²⁰	19.49	2.190×10 ⁻³	456.5